



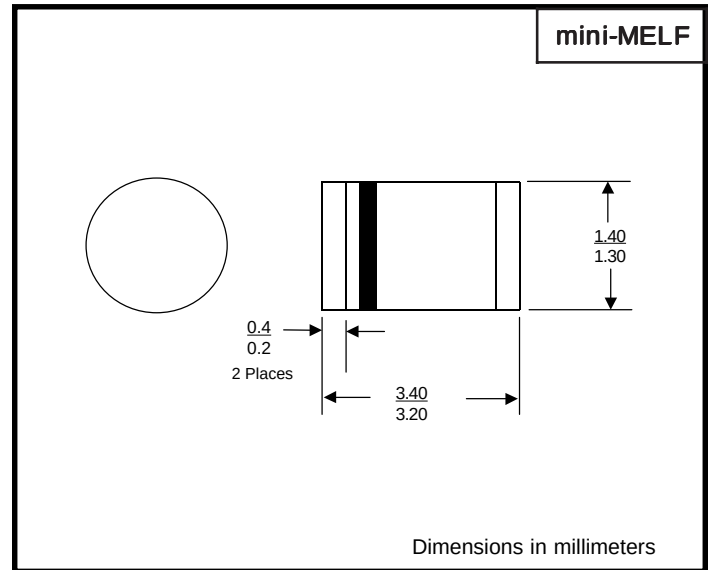
**1N4150 mini-MELF SIGNAL DIODE**

**Absolute Maximum Ratings (Ta=25°C)**

| Items                 | Symbol           | Ratings    | Unit |
|-----------------------|------------------|------------|------|
| Reverse Voltage       | VR               | 50         | V    |
| Reverse Recovery Time | trr              | 4          | ns   |
| Power Dissipation     | P <sub>tot</sub> | 500        | mW   |
| Forward Current       | IF               | 200        | mA   |
| Junction Temp.        | Tj               | -65 to 200 | °C   |
| Storage Temp.         | Tstg             | -65 to 200 | °C   |

**Mechanical Data**

| Items       | Materials                  |
|-------------|----------------------------|
| Package     | Mini MELF                  |
| Case        | Hermetically sealed glass  |
| Lead/Finish | Double stud/Solder Plating |
| Chip        | Glass Passivated           |



**Electrical Characteristics (Ta=25°C)**

| Ratings                                                               | Symbol  | Ratings | Unit  |
|-----------------------------------------------------------------------|---------|---------|-------|
| Minimum Breakdown Voltage<br>@IR= 100uA                               | BV      | 75      | V     |
| Peak Forward Surge Current<br>PW< 1sec.                               | IFsurge | 500     | mA    |
| Maximum Forward Voltage<br>IF= 200mA                                  | VF      | 1.0     | V     |
| Maximum Reverse Current<br>VR= 50V                                    | IR      | 100     | nA    |
| Maximum Junction Capacitance<br>VR= 0, f= 1 MHz                       | Cj      | 4       | pF    |
| Maximum Reverse Recovery Time<br>IF= 10mA, VR= 6V, IRR= 1mA, RL= 100Ω | trr     | 4       | ns    |
| Maximum Thermal Resistance                                            | RθJA    | 0.35    | °C/mW |